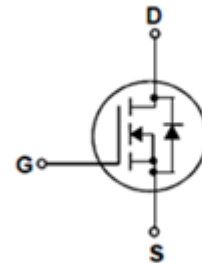
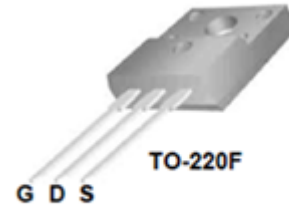


1200V N-Channel MOSFET

General Description

This Power MOSFET is produced using advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.



Features

3A, 1200V, $R_{DS(on)typ.} = 6\Omega @ V_{GS} = 10V$
 Low Gate Charge Minimize Switching Loss
 Fast Recovery Body Diode
 Improved dv/dt capability

Absolute Maximum Ratings $T_c = 25^\circ C$ unless otherwise noted

Symbol	Parameter	JFFM3N120E	Units
V_{DSS}	Drain – Source Voltage	1200	V
I_D	Drain Current Continuous ($T_c = 25^\circ C$)	3*	A
I_{DM}	Drain Current - Pulsed (Note 1)	12	A
V_{GSS}	Gate – Source Voltage	± 30	V
EAS	Single Pulsed Avalanche Energy (Note 2)	100	mJ
I_{AR}	Avalanche Current (Note 1)	3	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	20	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.0	V/ns
P_D	Power Dissipation ($T_c = 25^\circ C$)	30	W
	-Derate above $25^\circ C$	0.24	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum lead temperature for soldering purposes 1/8" from case for 5 seconds	300	$^\circ C$

*Drain current limited by maximum junction temperature.

Thermal characteristics

Symbol	Parameter	JFFM3N120E	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4.17	$^{\circ}\text{C}/\text{W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	--	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics $T_c = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	1200	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.6	--	$\text{V}/^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = 960\text{ V}, T_c = 125^{\circ}\text{C}$	--	--	1 100	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.5	--	4.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance	$V_{GS} = 10\text{ V}, I_D = 1.5\text{ A}$	--	6	7.5	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 1.5\text{ A}$ (Note 4)	--	4	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	--	860	--	pF
C_{oss}	Output Capacitance		--	22	--	pF
C_{rss}	Reverse Transfer Capacitance		--	60	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 600\text{ V}, I_D = 3.0\text{ A}, R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ (Note 4,5)	--	18	--	ns
t_r	Turn-On Rise Time		--	7	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	24	--	ns
t_f	Turn-Off Fall Time		--	11	--	ns
Q_g	Total Gate Charge	$V_{DS} = 600\text{ V}, I_D = 3.0\text{ A}, V_{GS} = 10\text{ V}$ (Note 4,5)	--	17.5	--	nC
Q_{gs}	Gate-Source Charge		--	5	--	nC
Q_{gd}	Gate-Drain Charge		--	5.5	--	nC
Drain – Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	3	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	12	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.0\text{ A}$	--	--	1.55	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 3.0\text{ A}$	--	195	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	0.75	--	μC

Notes:

1. Repetitive Rating : Pulsed width limited by maximum junction temperature
2. $L = 10.5\text{ mH}$, $I_{AS} = 3\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. $I_{SD} \leq 3.0\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$
4. Pulsed Test : Pulsed width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

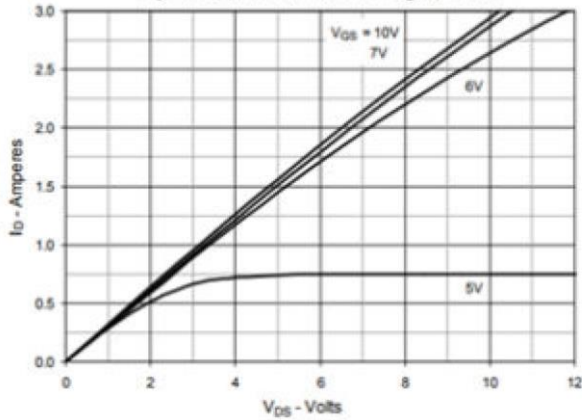


Figure 1. On-Region Characteristics

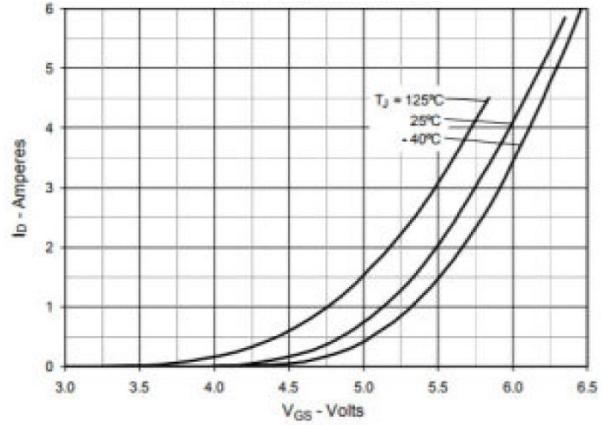


Figure 2. Transfer Characteristics

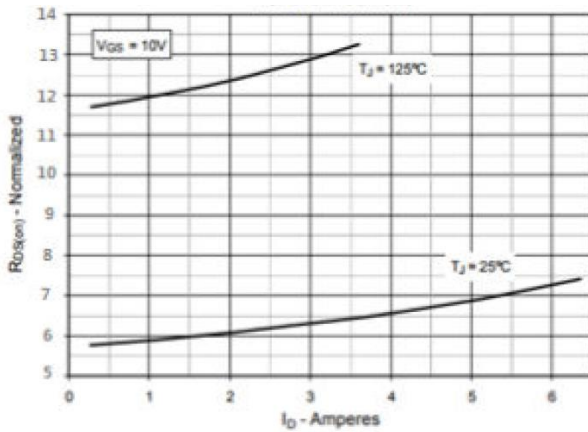


Figure 3. On-Resistance Variation vs Drain Current

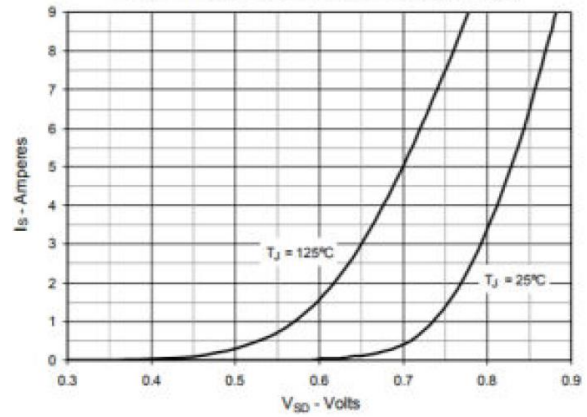


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

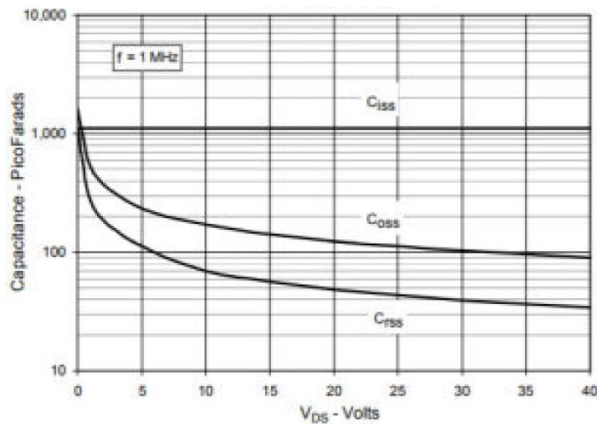


Figure 5. Capacitance Characteristics

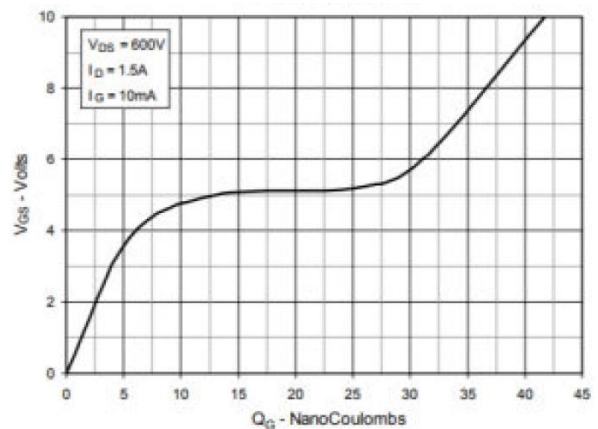


Figure 6. Gate Charge Characteristics

Typical Characteristics

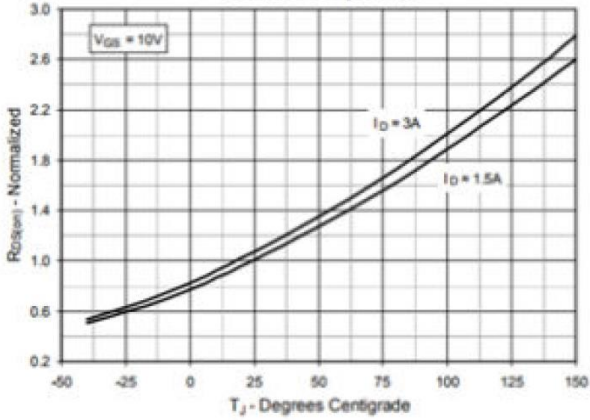


Figure 7. On-Resistance Variation vs Temperature

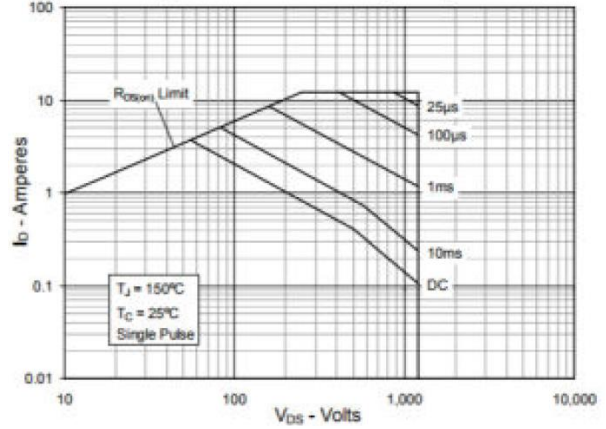


Figure 8. Maximum Safe Operating Area for JFFM3N120E

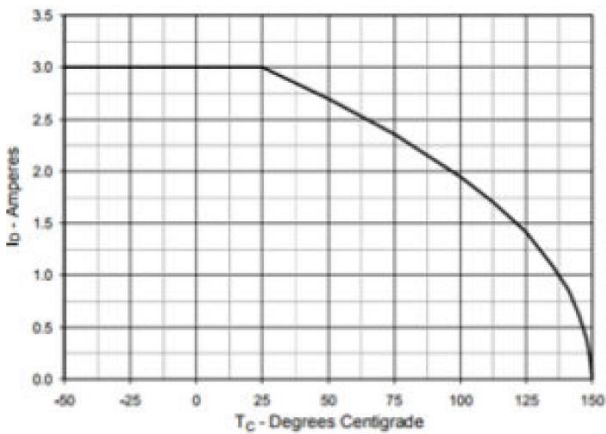


Figure 9. Maximum Drain Current vs Case Temperature

Typical Characteristics

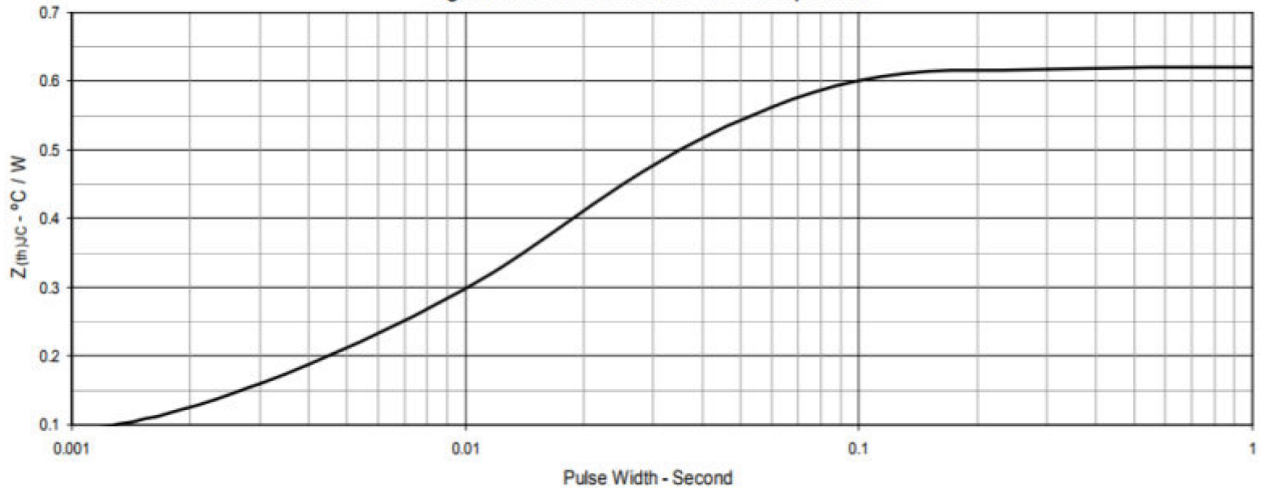
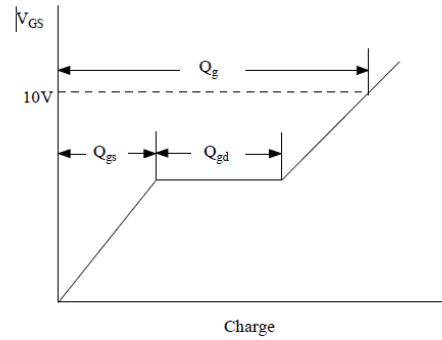
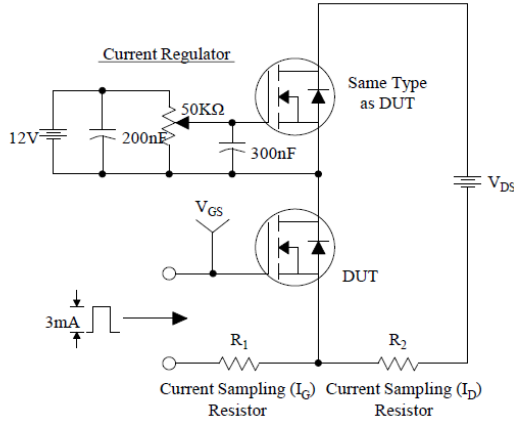
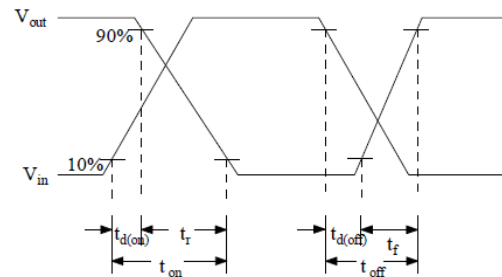
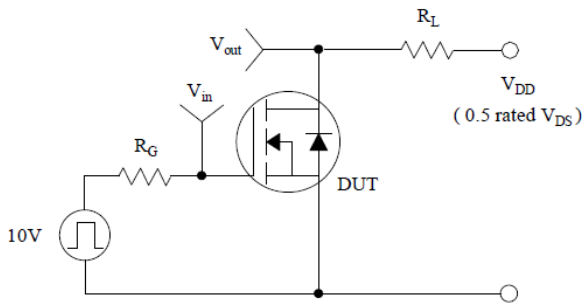


Figure 10. Transient Thermal Response Curve for JFFM3N120E

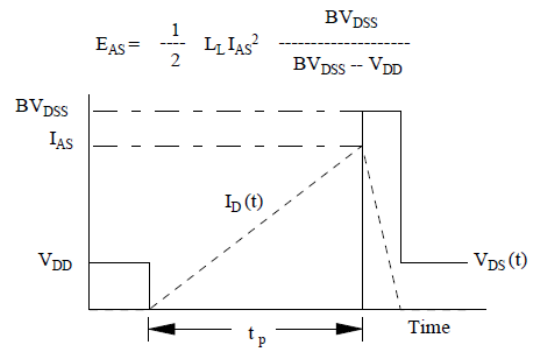
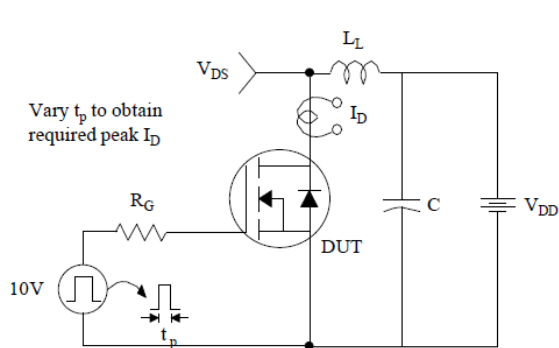
Test Circuit & Waveform



Gate Charge Test Circuit & Waveform

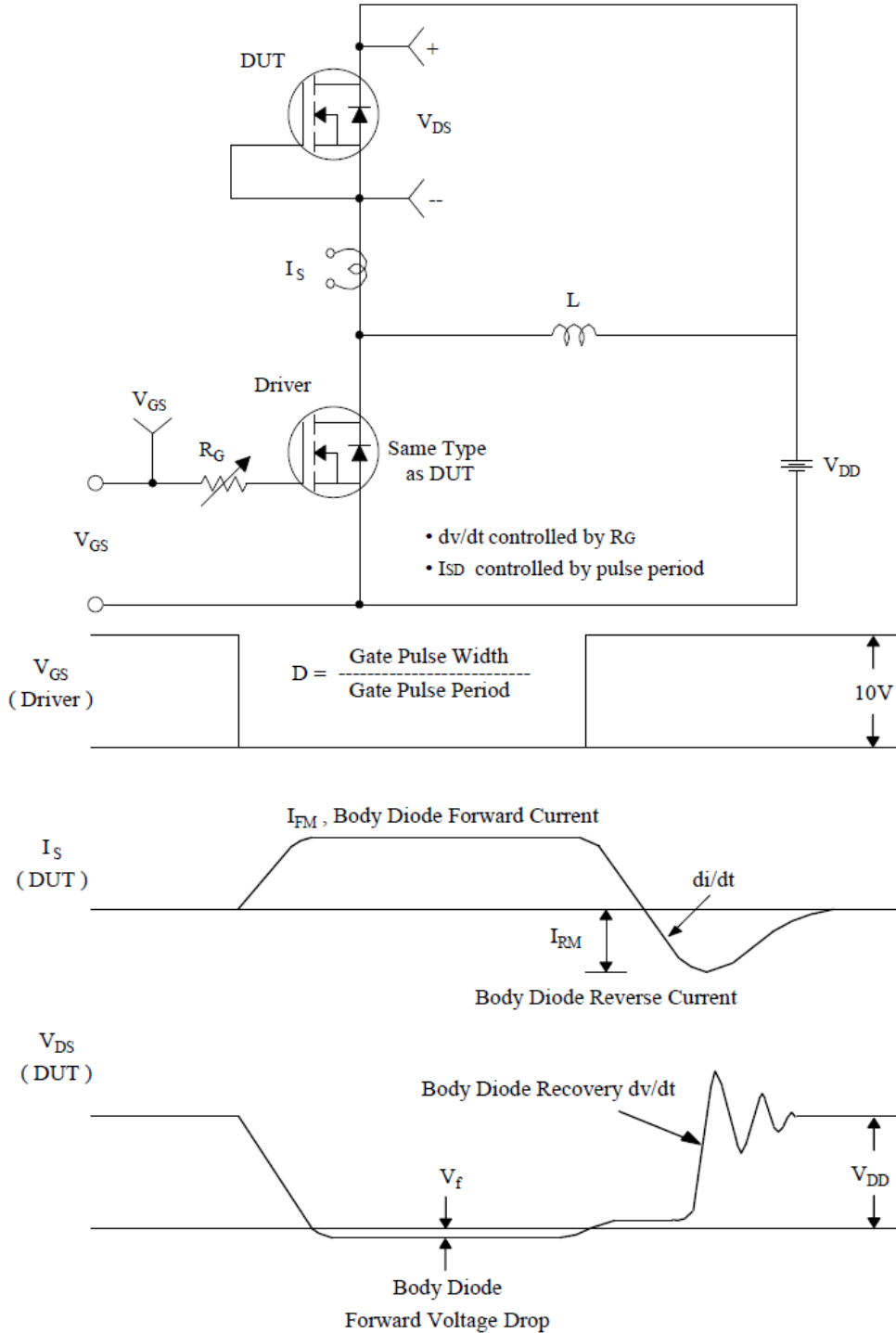


Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

Test Circuit & Waveform



Peak Diode Recovery dv/dt Test Circuit & Waveforms